

CoolMOS™ Power Transistor

Features

- New revolutionary high voltage technology
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge
- Ultra low effective capacitances
- Fully isolated package (2500 VAC; 1 minute)

CoolMOS™ 800V designed for:

- Industrial application with high DC bulk voltage
- Switching Application (i.e. active clamp forward)

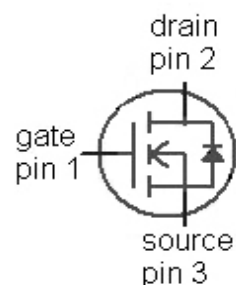
Product Summary

V_{DS}	800	V
$R_{DS(on)max}$ @ $T_j = 25^\circ\text{C}$	0.45	Ω
$Q_{g,typ}$	64	nC

PG-TO220FP



Type	Package	Marking
SPA11N80C3	PG-TO220FP	11N80C3



Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25^\circ\text{C}$	11	A
		$T_C=100^\circ\text{C}$	7.1	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	33	
Avalanche energy, single pulse	E_{AS}	$I_D=2.2\text{ A}$, $V_{DD}=50\text{ V}$	470	mJ
Avalanche energy, repetitive $t_{AR}^{2),3)}$	E_{AR}	$I_D=11\text{ A}$, $V_{DD}=50\text{ V}$	0.2	
Avalanche current, repetitive $t_{AR}^{2),3)}$	I_{AR}		11	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0\dots640\text{ V}$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f>1\text{ Hz}$)	± 30	
Power dissipation	P_{tot}	$T_C=25^\circ\text{C}$	41	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 150	$^\circ\text{C}$
Mounting torque		M2.5 screws	50	Ncm

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	$T_C=25\text{ °C}$	11	A
Diode pulse current ²⁾	$I_{S,pulse}$		33	
Reverse diode dv/dt ⁴⁾	dv/dt		4	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	3.7	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	80	
Soldering temperature, wave soldering only allowed at leads	T_{solder}	1.6 mm (0.063 in.) from case for 10s	-	-	260	°C

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	800	-	-	V
Avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}$, $I_D=11\text{ A}$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=0.68\text{ mA}$	2.1	3	3.9	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	-	20	μA
		$V_{DS}=800\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$	-	100	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=7.1\text{ A}$, $T_j=25\text{ °C}$	-	0.39	0.45	Ω
		$V_{GS}=10\text{ V}$, $I_D=7.1\text{ A}$, $T_j=150\text{ °C}$	-	1.05	-	
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	1.2	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	1600	-	pF
Output capacitance	C_{oss}		-	65	-	
Effective output capacitance, energy related ⁵⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	50	-	
Effective output capacitance, time related ⁶⁾	$C_{o(tr)}$		-	140	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=0/10\text{ V}, I_D=11\text{ A},$ $R_G=7.5\text{ }\Omega, T_j = 25^\circ\text{C}$	-	25	-	ns
Rise time	t_r		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	-	
Fall time	t_f		-	10	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD}=640\text{ V}, I_D=11\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	8	-	nC
Gate to drain charge	Q_{gd}		-	30	-	
Gate charge total	Q_g		-	64	85	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V

Reverse Diode

Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=I_S=11\text{ A},$ $T_j=25^\circ\text{C}$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V},$ $I_F=I_S=11\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	550	-	ns
Reverse recovery charge	Q_{rr}		-	10	-	μC
Peak reverse recovery current	I_{rrm}		-	33	-	A

¹⁾ J-STD20 and JESD22

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

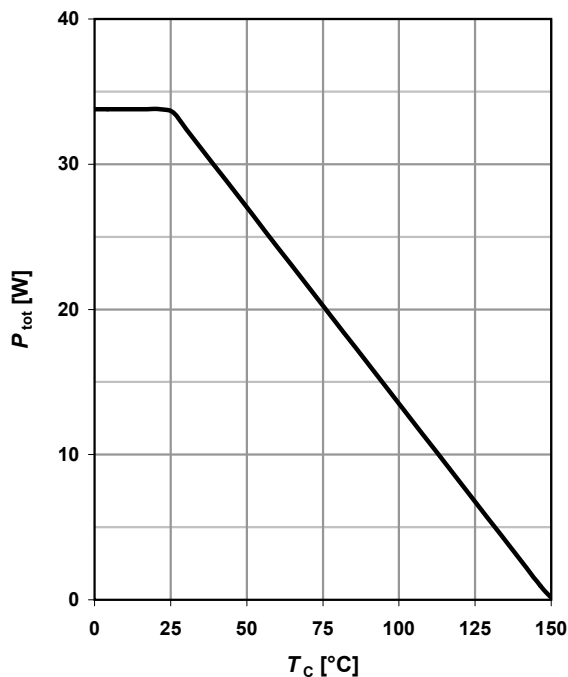
⁴⁾ $I_{SD} \leq I_D$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DClink} = 400\text{ V}$, $V_{peak} < V_{(BR)DSS}$, $T_j < T_{j,max}$, identical low side and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

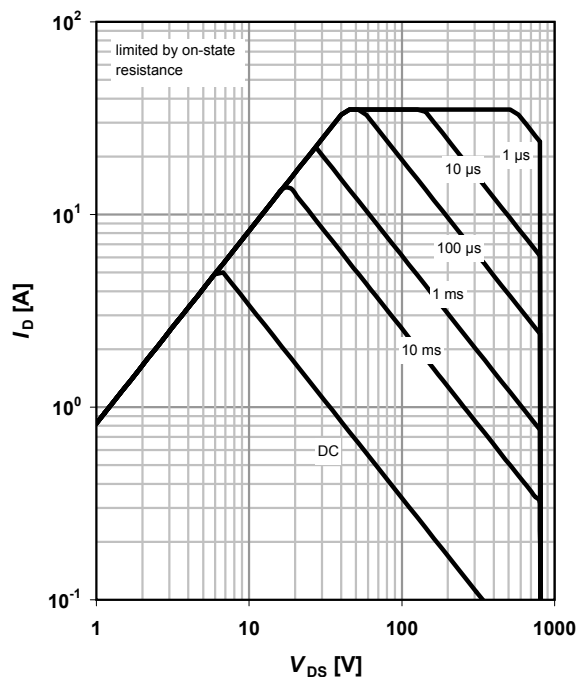
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

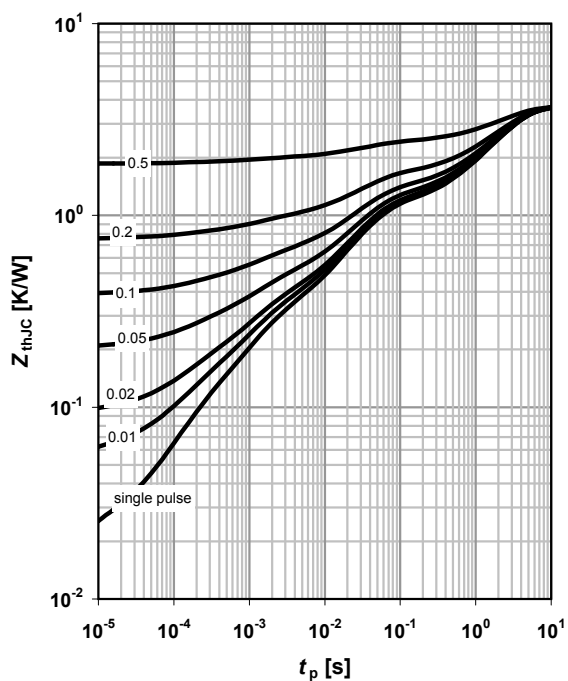
parameter: t_p



3 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

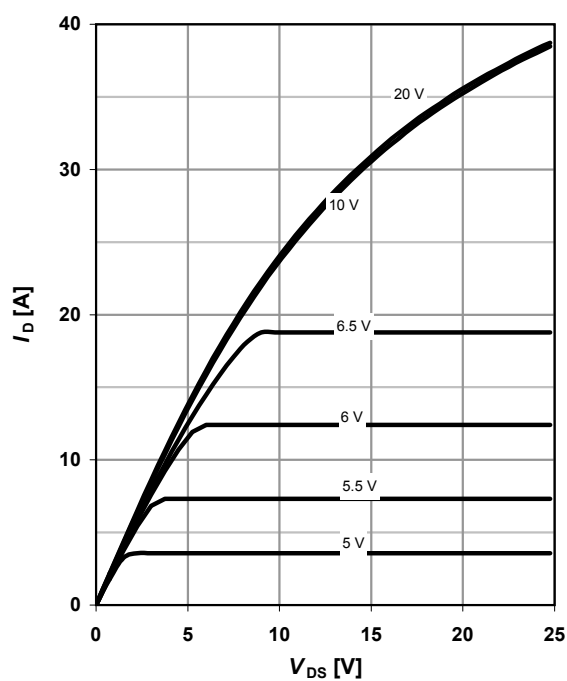
parameter: $D = t_p / T$



4 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}; t_p = 10 \mu\text{s}$$

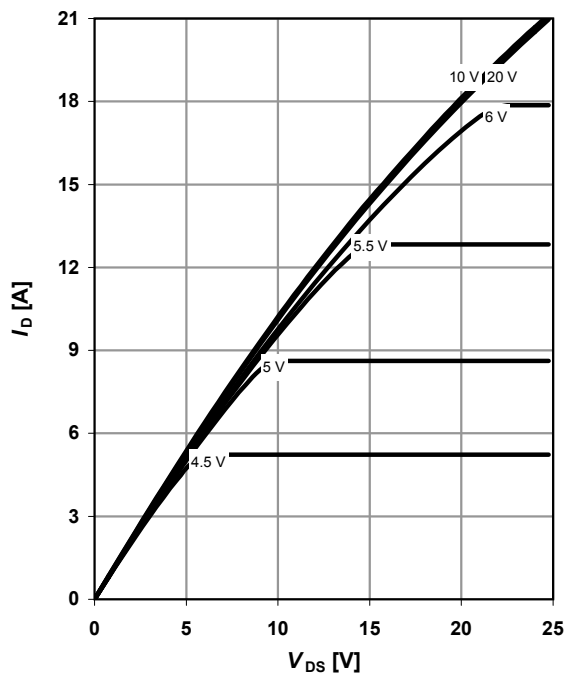
parameter: V_{GS}



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}; t_p = 10\ \mu\text{s}$$

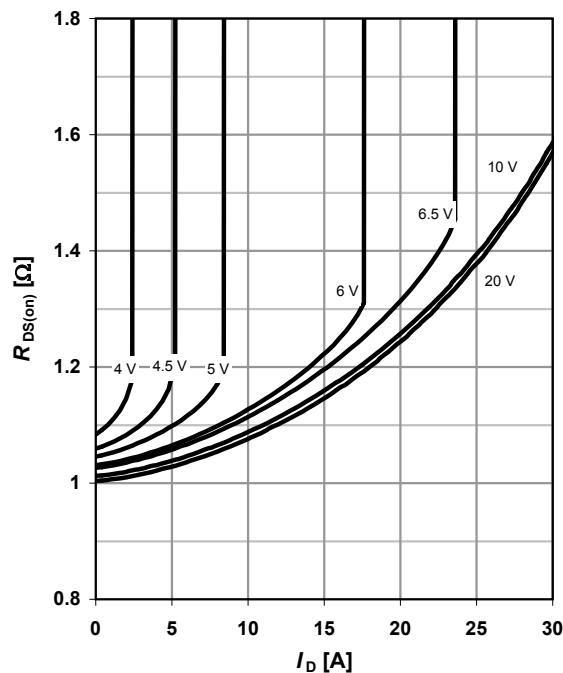
parameter: V_{GS}



6 Typ. drain-source on-state resistance

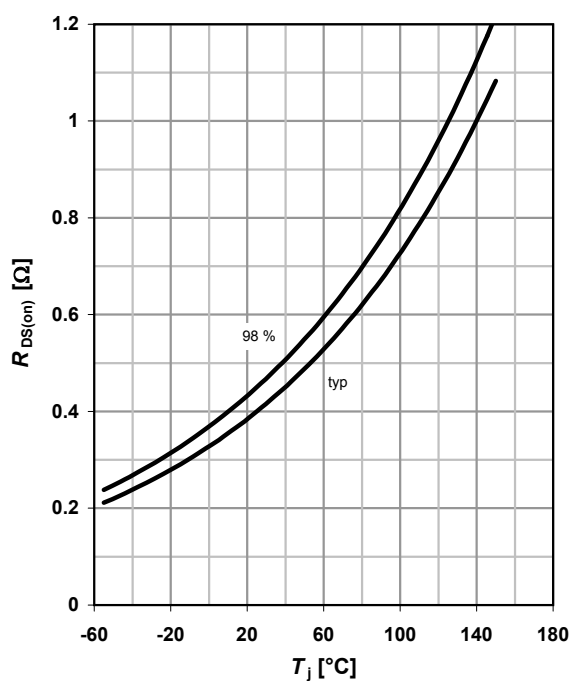
$$R_{DS(on)} = f(I_D); T_j = 150^\circ\text{C}$$

parameter: V_{GS}



7 Drain-source on-state resistance

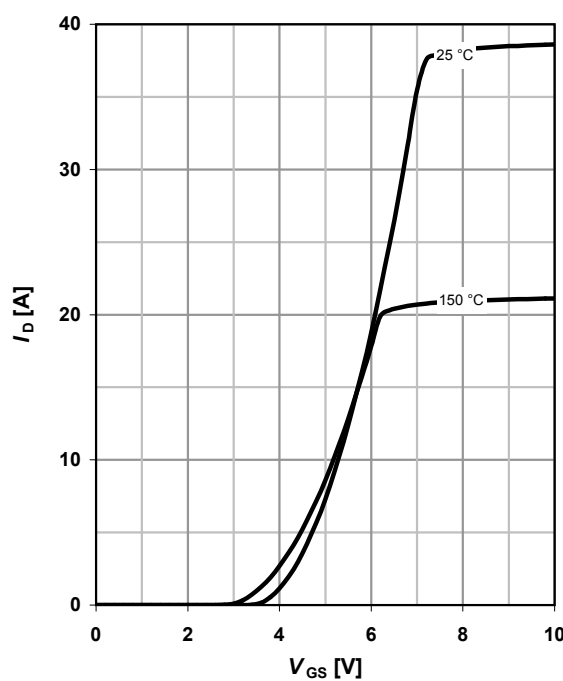
$$R_{DS(on)} = f(T_j); I_D = 7.1\ \text{A}; V_{GS} = 10\ \text{V}$$



8 Typ. transfer characteristics

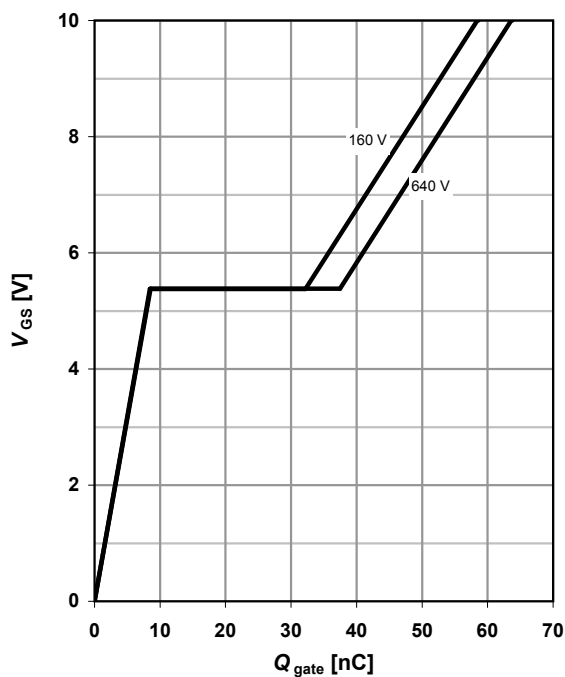
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|/R_{DS(on)\max}; t_p = 10\ \mu\text{s}$$

parameter: T_j



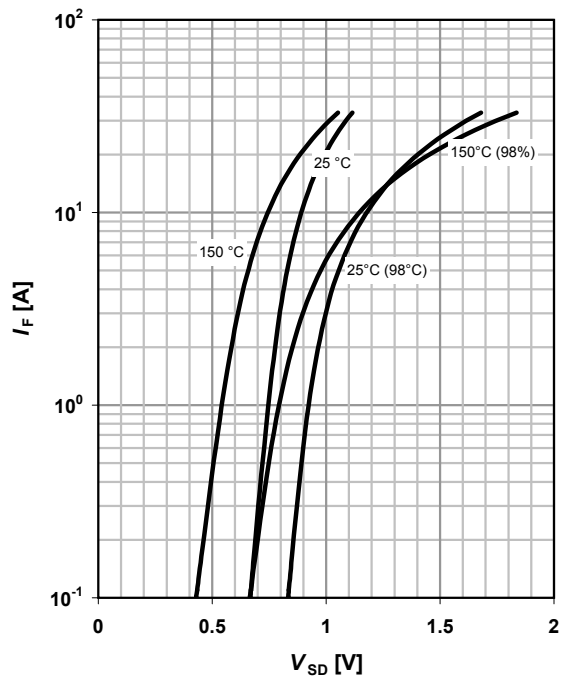
9 Typ. gate charge

 $V_{GS}=f(Q_{gate}); I_D=11\text{ A pulsed}$

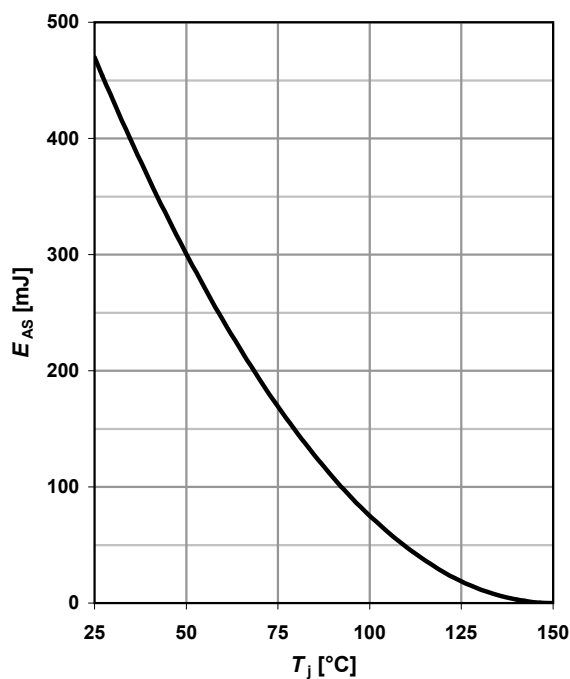
parameter: V_{DD}


10 Forward characteristics of reverse diode

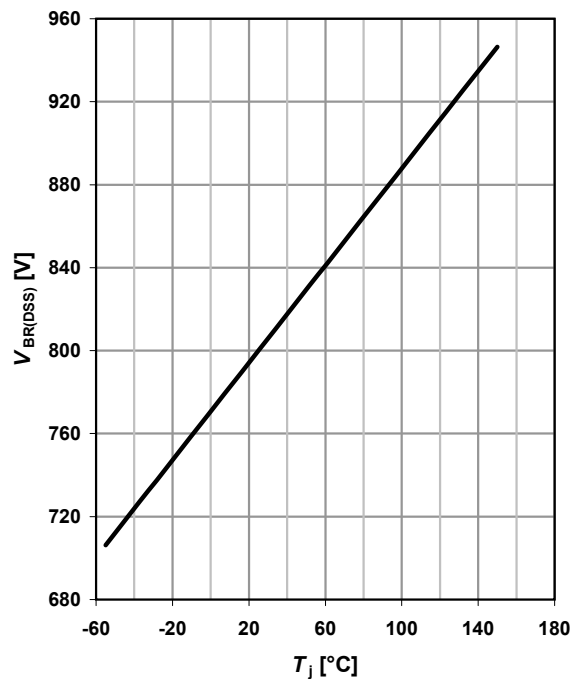
 $I_F=f(V_{SD}); t_p=10\text{ }\mu\text{s}$

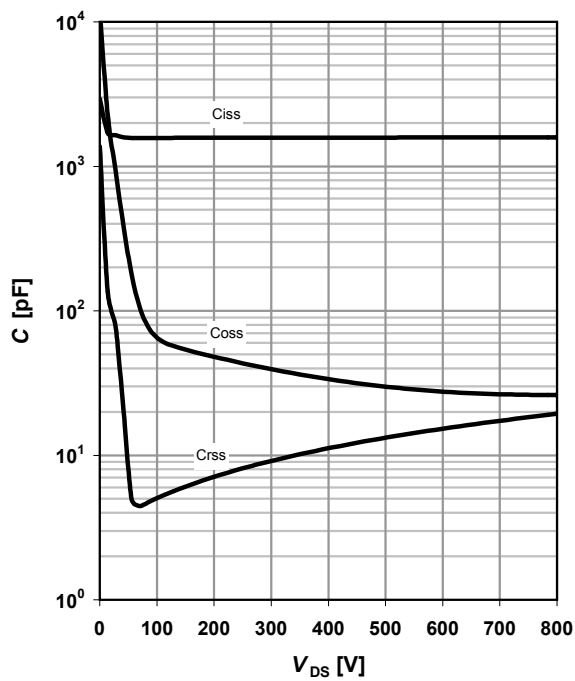
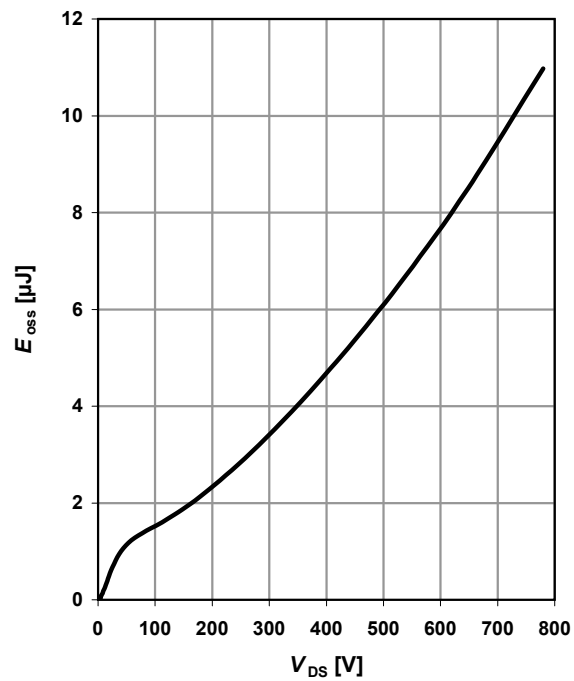
parameter: T_j


11 Avalanche energy

 $E_{AS}=f(T_j); I_D=2.2\text{ A}; V_{DD}=50\text{ V}$


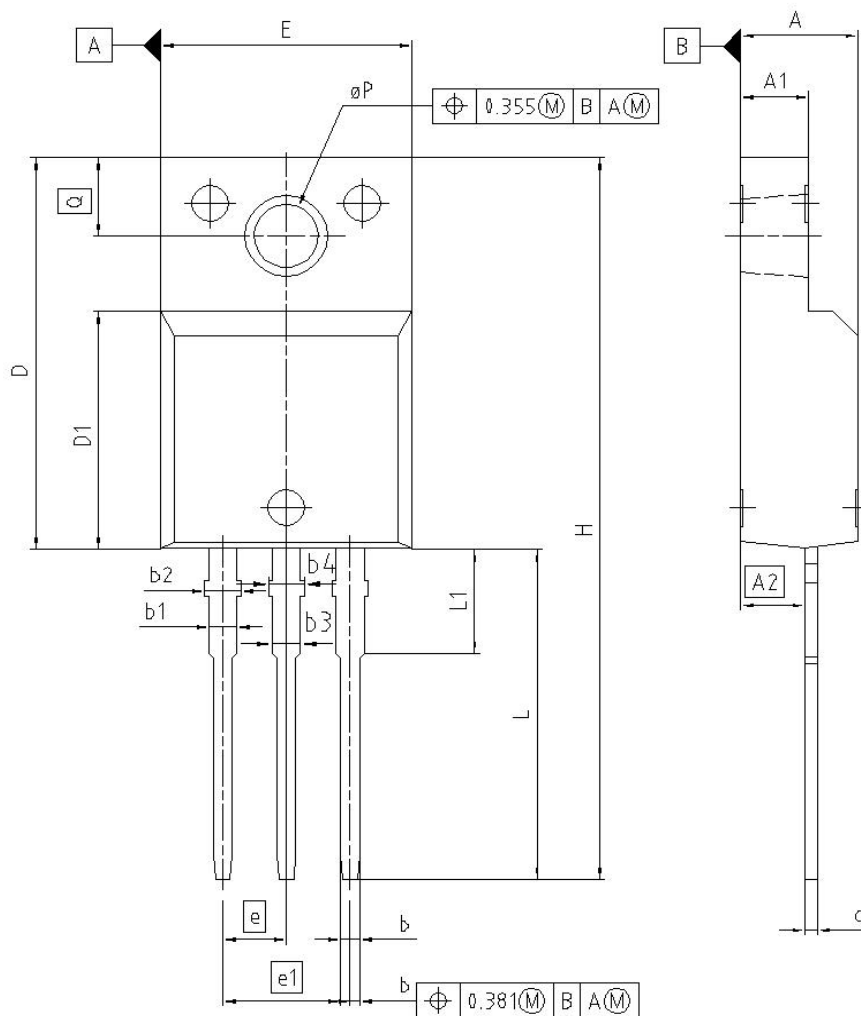
12 Drain-source breakdown voltage

 $V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$


13 Typ. capacitances
 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

14 Typ. Coss stored energy
 $E_{oss} = f(V_{DS})$


Definition of diode switching characteristics



PG-TO220FP: Outline


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.85	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

REFERENCE
...
SCALE
0 2.5 5mm
EUROPEAN PROJECTION

ISSUE DATE
08-01-2007
FILE
TO220_2

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Infineon Technologies AG
81726 Munich, Germany
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